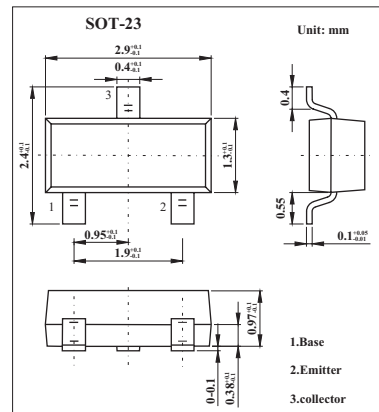


■ Features

- Low current (max. 100 mA)
- Low voltage (max. 50 V).



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	60	V
Collector-emitter voltage	V _{CEO}	50	V
Emitter-base voltage	V _{EBO}	6	V
Collector current (DC)	I _c	100	mA
Peak collector current	I _{CM}	200	mA
Peak base current	I _{BM}	100	mA
Total power dissipation Tamb ≤ 25°C; *	P _{tot}	250	mW
Storage temperature	T _{stg}	-65 to +150	°C
Junction temperature	T _j	150	°C
Operating ambient temperature	T _{amb}	-65 to +150	°C
Thermal resistance from junction to ambient *	R _{th j-a}	500	K/W

* Transistor mounted on an FR4 printed-circuit board.

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit	
Collector cut-off current	I _{CBO}	I _E = 0; V _{CB} = 60 V			10	nA	
		I _E = 0; V _{CB} = 60 V; T _j = 150°C			5	μA	
Emitter cut-off current	I _{EBO}	I _C = 0; V _{EB} = 5 V			10	nA	
DC current gain	h _{FE}	I _C = 2 mA; V _{CE} = 10 V; *	2PD601AQ	160		260	
			2PD601AR	210		340	
			2PD601AS	290		460	
DC current gain	h _{FE}	I _C = 100 mA; V _{CE} = 2 V;	90				
Collector-emitter saturation voltage	V _{CEsat}	I _C = 100 mA; I _B = 10 mA; *			500	mV	
Collector capacitance	C _c	I _E = i _e = 0; V _{CB} = 10 V; f = 1 MHz			3.5	pF	
Transition frequency	f _T	I _C = 2 mA; V _{CE} = 10 V; f = 100 MHz *	2PD601AQ	100			MHz
			2PD601AR	120			
			2PD601AS	140			

* Pulse test: t_p ≤ 300 μs; δ ≤ 0.02.

■ Marking

Type Number	2PD601AQ	2PD601AR	2PD601AS
Marking	ZQ	ZR	ZS